



10N65K

Power MOSFET

10A, 650V N-CHANNEL POWER MOSFET

DESCRIPTION

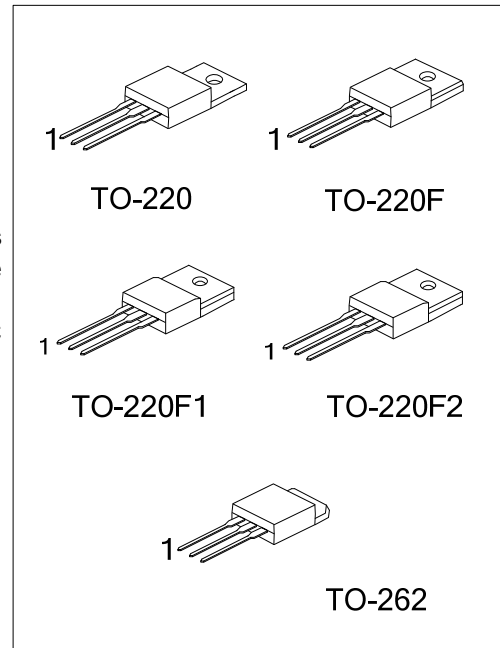
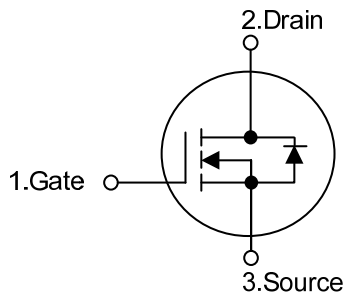
The UTC **10N65K** is an N-channel Power MOSFET using UTC's advanced technology to provide customers a minimum on-state resistance and superior switching performance, etc.

The UTC **10N65K** is generally applied in high efficient DC to DC converters, PWM motor controls and bridge circuits, etc.

FEATURES

- * $R_{DS(ON)} < 1.2\Omega$ @ $V_{GS} = 10V$
- * High Switching Speed
- * Improved dv/dt capability

SYMBOL



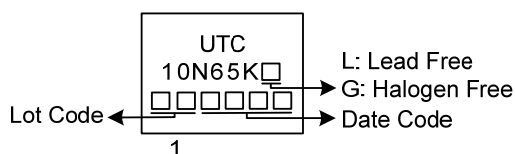
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10N65KL-TF3-T	10N65KG-TF3-T	TO-220F	G	D	S	Tube
10N65KL-TF1-T	10N65KG-TF1-T	TO-220F1	G	D	S	Tube
10N65KL-TF2-T	10N65KG-TF2-T	TO-220F2	G	D	S	Tube
10N65KL-T2Q-T	10N65KG-T2Q-T	TO-262	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

10N65KG-TF3-T (1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube (2) TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2 T2Q: TO-262 (3) G: Halogen Free and Lead Free, L: Lead Free
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MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DS}	650	V
Gate-Source Voltage		V_{GS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	10	A
Drain Current	Continuous	I_D	10	A
	Pulsed (Note 2)	I_{DM}	38	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	300	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220/TO-262	P_D	156	W
	TO-220F/TO-220F1		50	
	TO-220F2		52	
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L=6\text{mH}$, $I_{AS}=10\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 9.5\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		θ_{JA}	65.2	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220/TO-262	θ_{JC}	0.8	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		2.5	
	TO-220F2		2.4	

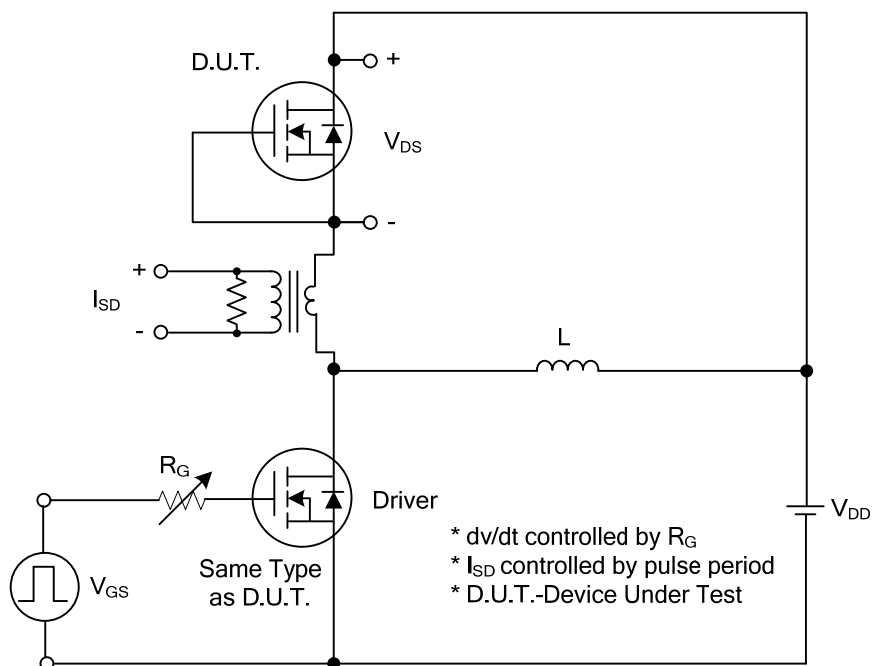
■ **ELECTRICAL CHARACTERISTICS** ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0V, I _D = 250μA	650			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 650V, V _{GS} = 0V			1	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
	Reverse		V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
Breakdown Voltage Temperature Coefficient		ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.7		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} = 10V, I _D = 5A	0.5	0.89	1.2	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0 MHz		1200	1700	pF
Output Capacitance		C _{OSS}			110	160	pF
Reverse Transfer Capacitance		C _{RSS}			10.5	16	pF
SWITCHING CHARACTERISTICS							
Total Gate Charge		Q _G	V _{DS} =50V, I _D =1.3A, V _{GS} =10 V (Note 1, 2)		31.3	42	nC
Gate-Source Charge		Q _{GS}			9.3		nC
Gate-Drain Charge		Q _{GD}			6.8		nC
Turn-On Delay Time		t _{D(ON)}	V _{DD} =30V, I _D =0.5A, R _G =25Ω (Note 1, 2)		75		ns
Turn-On Rise Time		t _R			60		ns
Turn-Off Delay Time		t _{D(OFF)}			180		ns
Turn-Off Fall Time		t _F			65		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Maximum Continuous Drain-Source Diode Forward Current		I _S				10	A
Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}				38	A
Drain-Source Diode Forward Voltage		V _{SD}	V _{GS} = 0 V, I _S =10A			1.4	V

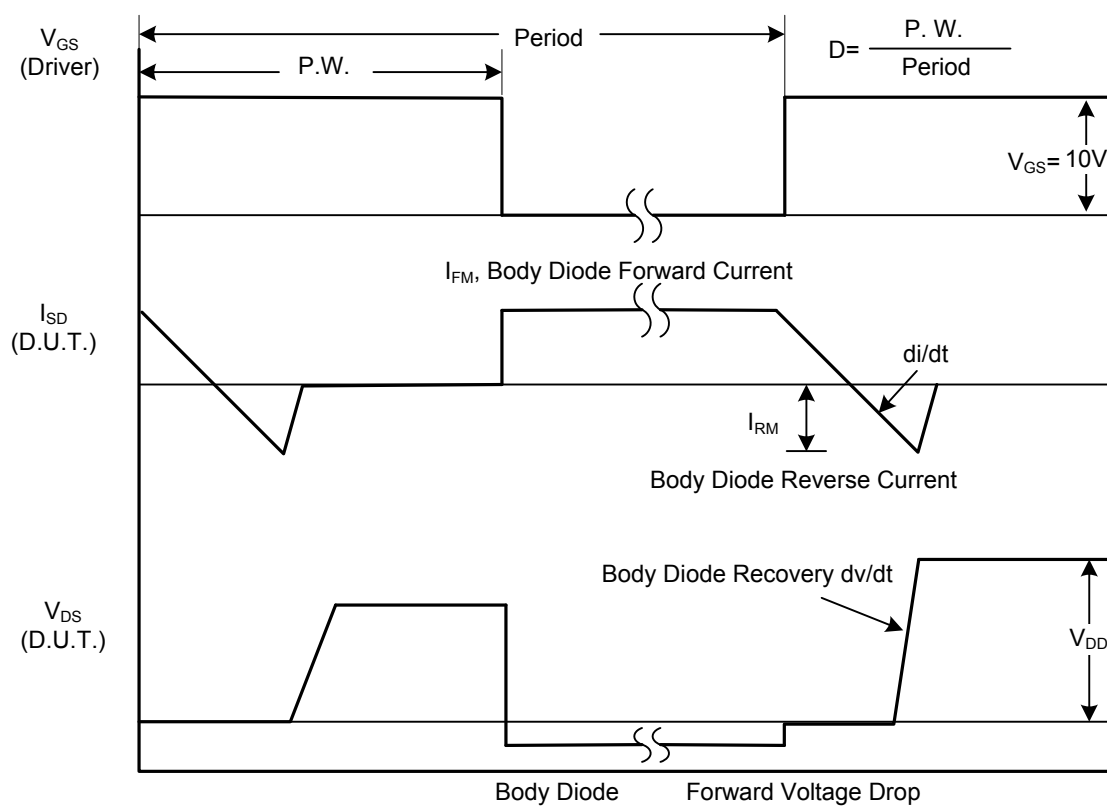
Note: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

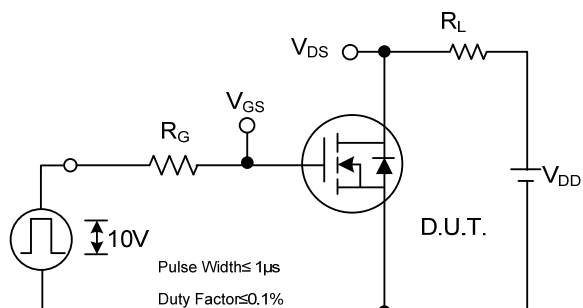


Peak Diode Recovery dv/dt Test Circuit

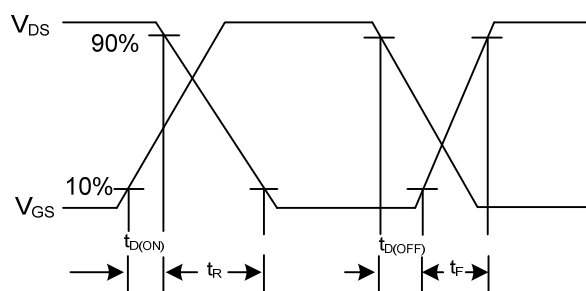


Peak Diode Recovery dv/dt Waveforms

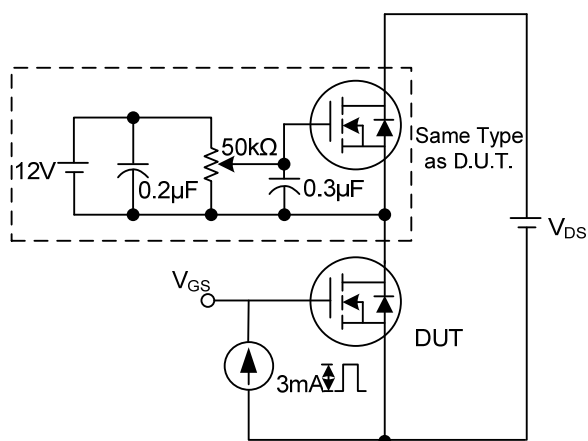
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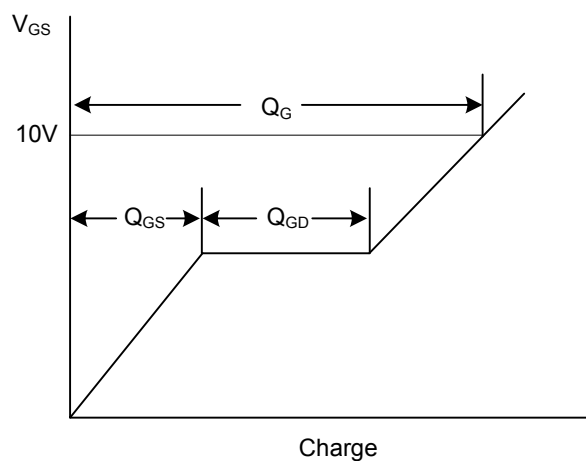
Switching Test Circuit



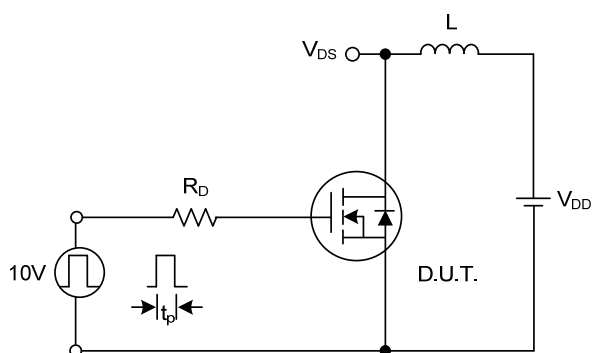
Switching Waveforms



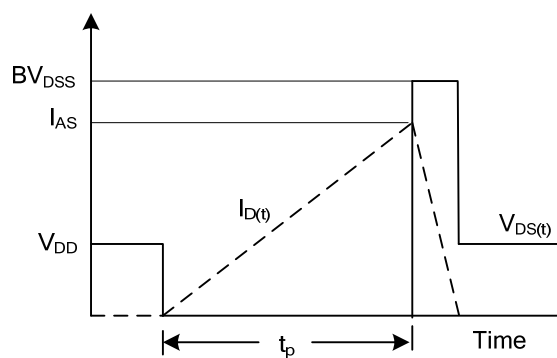
Gate Charge Test Circuit



Gate Charge Waveform

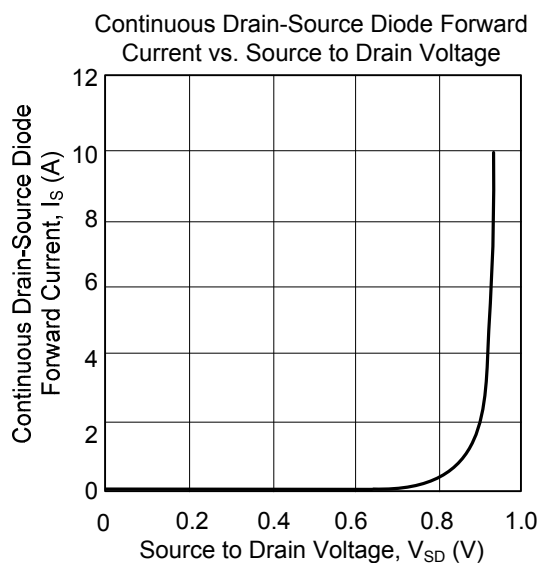
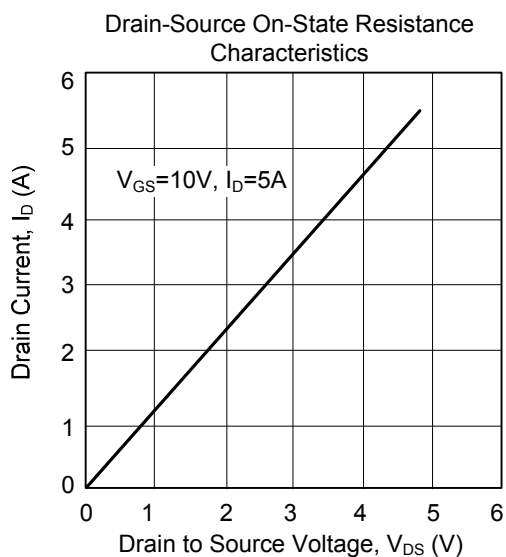
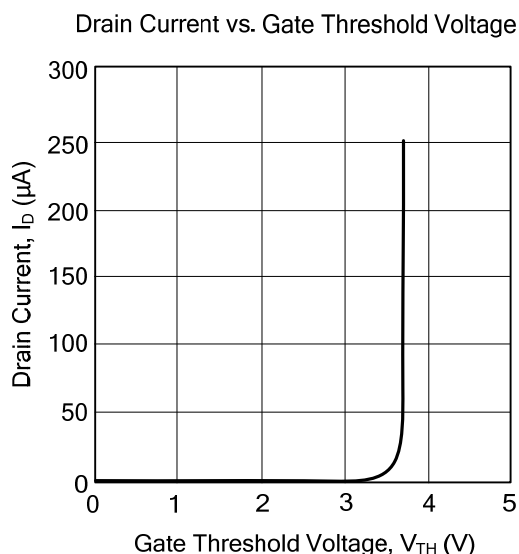
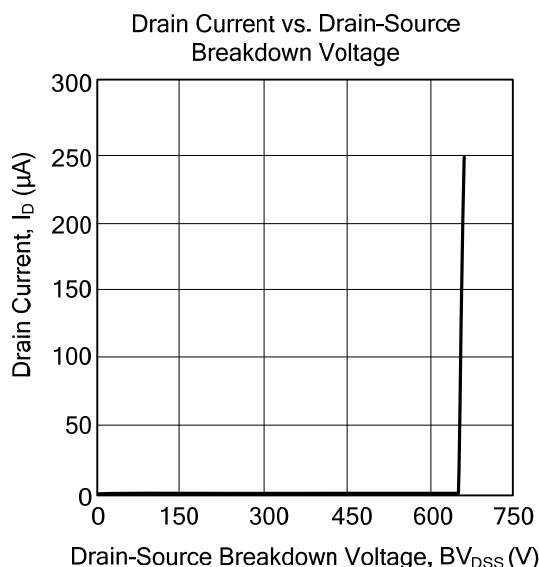


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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